

**Amendments to the Claims:**

Claims 1-42 (Canceled).

43. (Previously Presented): An ion implant lithography method of processing a semiconductor substrate comprising:

forming a layer to be etched over a semiconductor substrate;

forming an imaging layer of a selected thickness over the layer to be etched;

ion implanting selected regions of the imaging layer to change solvent solubility of implanted regions versus non-implanted regions of the imaging layer, said ion implanting forming innermost peak implant concentrations which are spaced elevationally outward from the layer to be etched;

removing the ion implanted regions of the imaging layer to leave a pattern of openings in the imaging layer; and

after the removing, etching the layer to be etched through the imaging layer openings using the imaging layer as an etch mask by first blanket etching the imaging layer and the layer to be etched using an etch chemistry that is substantially selective to the imaging layer and then etching into the layer to be etched substantially selectively to the imaging layer.

44. (Previously Presented): The method of claim 43 wherein the imaging layer is organic.

45. (Previously Presented): The method of claim 43 wherein the imaging layer comprises organic photoresist.

46. (Previously Presented): The method of claim 43 wherein the ion implanting forms the selected regions to have innermost peak implant concentrations which are spaced elevationally outward of the layer to be etched by about 50 Angstroms to about 5000 Angstroms.

47. (Currently Amended): The method of claim 43 wherein the ion implanting forms the selected regions to have innermost peak implant concentrations which are spaced elevationally outward of the layer to be etched by about 200 Angstroms to about 2000 Angstroms.

48. (Currently Amended): The method of claim 43 wherein the ion implanting forms the selected regions to have innermost peak implant concentrations which are spaced elevationally outward of the layer to be etched by about ~~200 Angstroms to about 2000 Angstroms~~ 400 Angstroms to about 800 Angstroms.

49. (Previously Presented): The method of claim 43 wherein the imaging layer consists essentially of organic photoresist.

50. (Previously Presented): The method of claim 43 wherein the imaging layer consists essentially of a single, homogeneous layer.

51. (Previously Presented): The method of claim 43 wherein the layer to be etched is conductive.

52. (Previously Presented): The method of claim 43 wherein the layer to be etched is semiconductive.

53. (Previously Presented): The method of claim 43 wherein the layer to be etched is insulative.

54. (Previously Presented): The method of claim 43 wherein the layer to be etched comprises polysilicon.

55. (Previously Presented): The method of claim 43 wherein the removing comprises wet solvent processing.

56. (Previously Presented): The method of claim 43 wherein the ion implanting comprises hydrogen ions.

57. (Previously Presented): The method of claim 43 wherein the ion implanting comprises helium ions.

58. (Currently Amended): The method of claim 43 wherein the semiconductor ~~substrate comprises silicon~~ substrate comprises silicon.

59. (New): The method of claim 43 wherein the semiconductor substrate comprises bulk monocrystalline silicon.

60. (New): The method of claim 43 wherein the imaging layer is of a thickness of about 10,000 Angstroms.

61. (New): The method of claim 43 wherein the etching with the etch chemistry is of a selectivity to the imaging layer of about 3:1.